IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

U.S. Patent No.: 7.273.533

Issue Date: September 25, 2007 Serial No.: 10/717,268

Applicants: Brcka et al.

Title: PLASMA PROCESSING SYSTEM WITH LOCALLY-EFFICIENT

INDUCTIVE PLASMA COUPLING

Attorney Docket: TAZ-248

Confirmation No.: 7396

Cincinnati, Ohio 45202 September 13, 2008

VIA ELECTRONIC FILING

Certificate of Corrections Branch

Commissioner for Patents

P.O. Box 1450 Alexandria, VA 22313-1450

Sir

REQUEST FOR CERTIFICATE OF CORRECTION (37 CFR §§ 1.322(a), 1.323)

It is respectfully requested that a Certificate of Correction be issued for the aboveidentified patent. The patent contains errors that occurred through the fault of the U.S. Patent and Trademark Office. The patent also contains errors that occurred by Applicants in the specification.

Form PTO/SB/44 outlining the corrections to be made is submitted herewith.

Applicants submit herewith the fee of \$100 due as a result of this request. If any deficiencies or credits are necessary to complete this communication, please apply them to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

By: /Joseph R. Jordan/

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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PATENT NO :	7,273,533	
APPLICATION NO.:	10/717,268	
ISSUE DATE :	September 25, 2007	
INVENTOR(S) :	Brcka et al.	
	d that an error appears or errors appear in the above-identified patent and t ted as shown below:	nat said Letters Patent
6,685,799 B2 Col. 2, line 31, 'Col. 2, line 35, 'Col. 2, line 39, 'Col. 2, line 51, 'Col. 5, line 4, 'Tol. 5, line 23, 'Col. 10, line 3,	der the "References Cited" section, "6,685,799 B2" 2/2004 Hooshdaran e * 2/2004 Davis et al.— torroids, "should read -toroids, by the present applicant" should read -by the present applicants are becoming of increase demand" should read -are becoming of increase processing of 300 mm wafer." should read -processing of 300 mm wafers. wif flux channels, are" should read -low flux channels are Applicant has proposed" should read -Applicants have proposed of the rf power deposited into" should read -of the RF power deposited into "(FIG. 20 and 2F)" should read -(FIGS. 2D and 2F)	ed demand

MAILING ADDRESS OF SENDER (Please do not use customer number below):

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This collection of information is required by 37 GFR 1,322, 1,323, and 1,324. The information is required to obtain or retain a benefit by the public which is to file and by the USPTO to process) an application Confidentially is governed by 3 (19 and 19 comments on the amount of time you require to complete this form and/or suggestions for reducing the burden, should be sent to the Chell Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA. 22313-1450, DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS, SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.